



N-CHANNEAL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _{D MAX} Ta = +25°C
	$29m\Omega @ V_{GS} = 4.5V$	5.6A
12V	$34m\Omega @ V_{GS} = 2.5V$	5.1A
1∠V	44mΩ @ V _{GS} = 1.8V	4.5A
	65mΩ @ V _{GS} = 1.5V	3.7A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

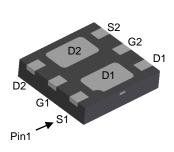
Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

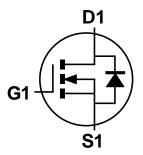
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

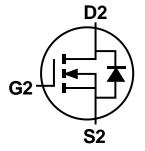
U-DFN2020-6 (Type B)



Bottom View



Q1 N-CHANNEL MOSFET



Q2 N-CHANNEL MOSFET

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1029UFDB -7	U-DFN2020-6 (Type B)	3000/Tape & Reel
DMN1029UFDB -13	U-DFN2020-6 (Type B)	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Kev

Date Code Ney												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н	ı	J	K	L	М	N	0	Р	R
									I.		1	I.
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



D5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Kev

Date Code Hoy											
Year	2015	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	Χ	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	5.6 4.4	А
Continuous Diain Current (Note 5) VGS = 4.5V	t < 5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lο	7.2 5.8	А
Maximum Continuous Body Diode Forward Curre	ent (Note 5)		Is	1	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle =	1%)		Ірм	20	Α
Avalanche Current (L = 0.1mH)			I _{AS}	15	А
Avalanche Energy (L = 0.1mH)			Eas	12	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
Total Bayer Dissination (Note 5)	Steady State	ק	1.4	W	
Total Power Dissipation (Note 5)	t < 5s	P_D	2.2	VV	
Thermal Peciatones, Jungtion to Ambient (Note 5)	Steady State		91		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	$R_{\theta JA}$	55	°C/W	
Thermal Resistance, Junction to Case	$R_{\theta JC}$	20			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

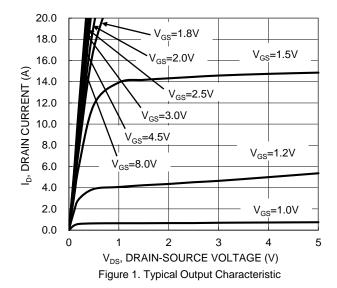
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BVDSS	12	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	1.0	μΑ	V _{DS} = 12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)	•					•
Gate Threshold Voltage	Vgs(TH)	0.4	_	1	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
		_	17	29		$V_{GS} = 4.5V, I_{D} = 5A$
Static Drain-Source On-Resistance		_	20	34	mΩ	$V_{GS} = 2.5V, I_{D} = 4.6A$
Static Drain-Source On-Resistance	RDS(ON)	_	24	44	11177	$V_{GS} = 1.8V, I_D = 4.1A$
		_	30	65		V _G S = 1.5V, I _D = 2A
Diode Forward Voltage	Vsp	_	0.6	1.2	V	V _G S = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)	•					•
Input Capacitance	Ciss	_	914	_	pF	., ., ., ., .,
Output Capacitance	Coss	_	132	_	pF	V _{DS} = 6V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	119	_	pF	T = 1.0WHZ
Gate Resistance	Rg	_	1.26	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)		_	10.5	_	nC	
Total Gate Charge (VGS = 8V)	Qg	_	19.6	_	nC	7, 0, 1, 0, 5,
Gate-Source Charge	Qgs	_	1.2	_	nC	$V_{DS} = 6V, I_{D} = 6.5A$
Gate-Drain Charge	Qgd	_	1.6	_	nC	7
Turn-On Delay Time	t _{D(ON)}	_	5.0	_	ns	
Turn-On Rise Time	t _R	_	10.5	_	ns	V _{DD} = 6V, V _{GS} = 4.5V,
Turn-Off Delay Time	tD(OFF)	_	16.6	_	ns	$R_L = 1.2\Omega, R_g = 1\Omega$
Turn-Off Fall Time	t _F	_	4.1	_	ns	7

5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





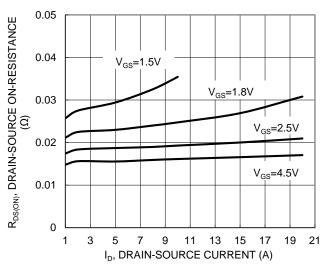


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

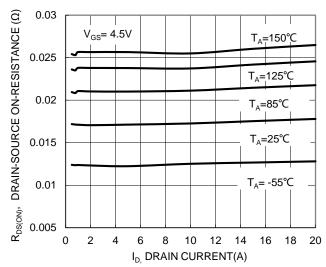
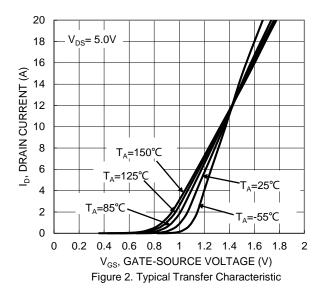
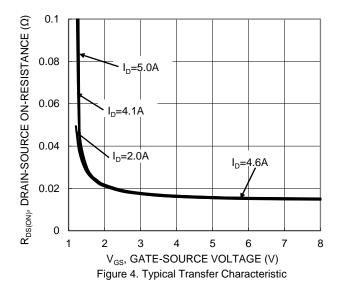


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





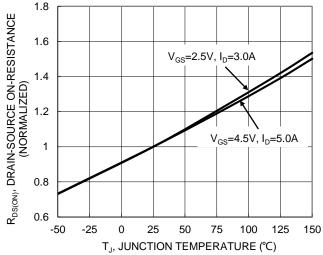


Figure 6. On-Resistance Variation with Temperature



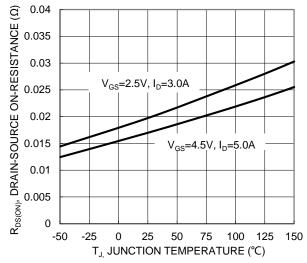
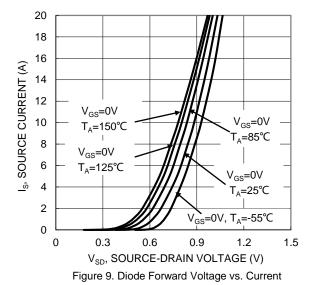
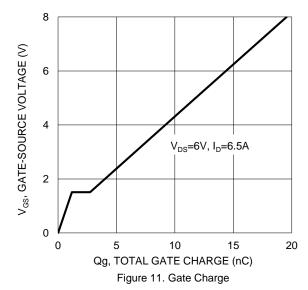


Figure 7. On-Resistance Variation with Temperature





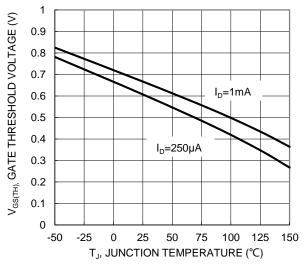


Figure 8. Gate Threshold Variation vs. Junction Temperature

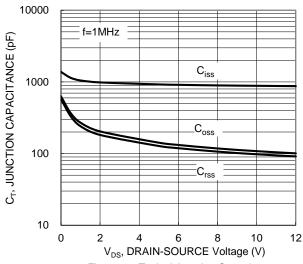


Figure 10. Typical Junction Capacitance

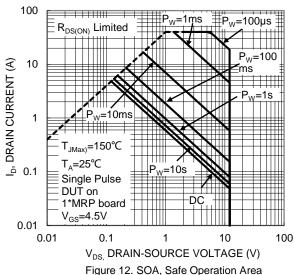


Figure 12. SOA, Sare Operation Area



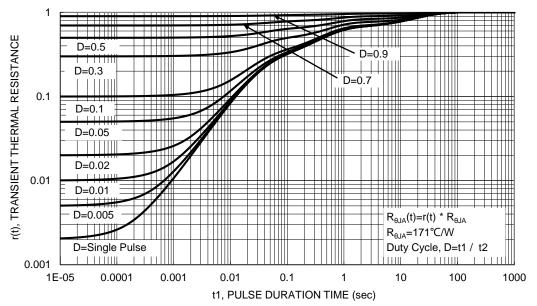


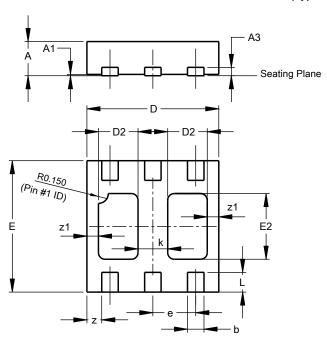
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

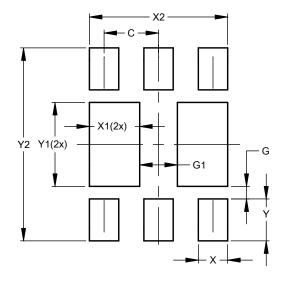


	U-DFN2020-6 Type B							
Dim	Min							
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
A3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	2 0.50 0.70		0.60					
е	-	_	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	-	-	0.45					
L	0.25	0.35	0.30					
Z	-		0.225					
z1	-	-	0.175					
All I	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value		
Dilliensions	(in mm)		
С	0.650		
G	0.150		
G1	0.450		
X	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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